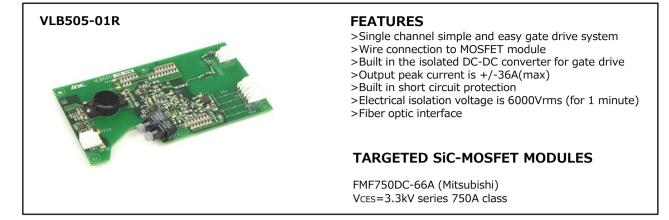
Oct.2020



VLB505-01R

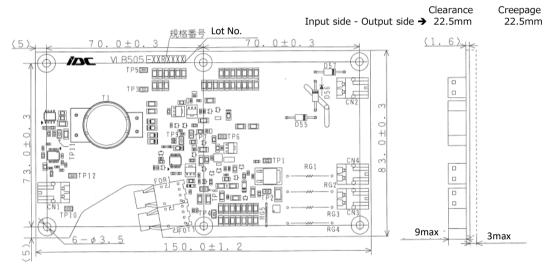
DRIVER FOR SIC-MOSFET MODULES

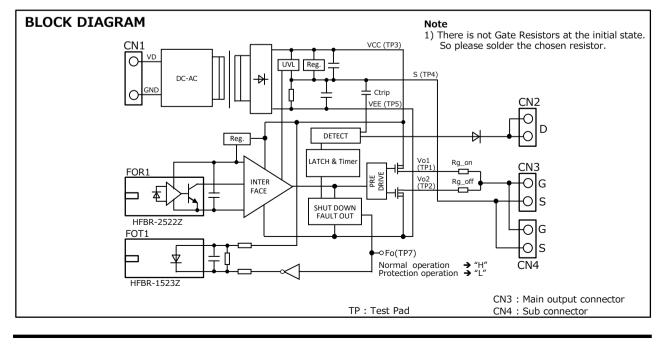


APPLICATIONS

Medium voltage inverter , HVDC infrastructure , Traction or Wind power etc.

OUTLINE





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DRIVER FOR SIC-MOSFET MODULES

MAXIMUM RATINGS

Symbol	Parameter	Parameter Conditions		Unit
VD	Supply voltage	Supply voltage Between VD and GND		V
IOHP		Dulas width 200	-36	А
IOLP	Output peak current	Pulse width 3us	36	А
Viso	Isolation voltage between primary and secondary			Vrms
Tc	Case temperature	Surface temperature of power MOSFET	100	deg C
Topr	Operating temperature No condensation allowable		-40 ~ 85	deg C
Tstg	Storage temperature	No condensation allowable	-40 ~ 85	deg C
Idrive	Gate drive current	Gate average current	200	mA
VC	Peak collector voltage	Peak terminal voltage of CN2	3300	V

(unless otherwise noted, Ta=25 $^{\circ}$ C)

ELECTRICAL CHARACTERISTICS (unless otherwise noted, Ta=25°C,VD=15V, Rg_on=2Ω,Rg_off=1Ω, f=3kHz)

Gurahal	Davaaraahar	Conditions	Limits			11
Symbol	Parameter	Conditions		Тур	Max	Unit
VD	Supply voltage	Recommended range	14.5	15	15.5	V
f	Switching frequency	Recommended range It is limited by gate average current (max:200mA)	-	-	10	kHz
RG	Gate resistance	Recommended range (Total compound value)	0.22	-	-	Ω
VOH	Plus bias output voltage	Idrive = 0 ~ 200mA	16	17	18	V
VOL	Minus bias output voltage	Idrive = $0 \sim 200$ mA	-	-11	-	V
tPLH	"L-H" propagation time	IF=30mA, Fiber length=50cm, C_load:0.57uF	0.2	0.4	0.8	us
tPHL	"H-L" propagation time	IF=30mA, Fiber length=50cm, C_load:0.57uF	0.1	0.3	0.5	us
ttimer	Timer	Between start and cancel of protection (Under input signal is off state)	1	-	2	ms
ttrip	Masked time detect short circuit	Detect terminal (CN2) : over than 15V or open	-	3	-	us
VSC	SC detect voltage	Drain voltage of MOSFET	15	-	-	V
UVLO+_VCC	Under voltage lock out (Operation start)	VCC voltage	-	14.4	-	v
UVLOVCC	Under voltage lock out (Operation stop)	VCC voltage	-	13.8	-	v

<Gate Drive Unit>

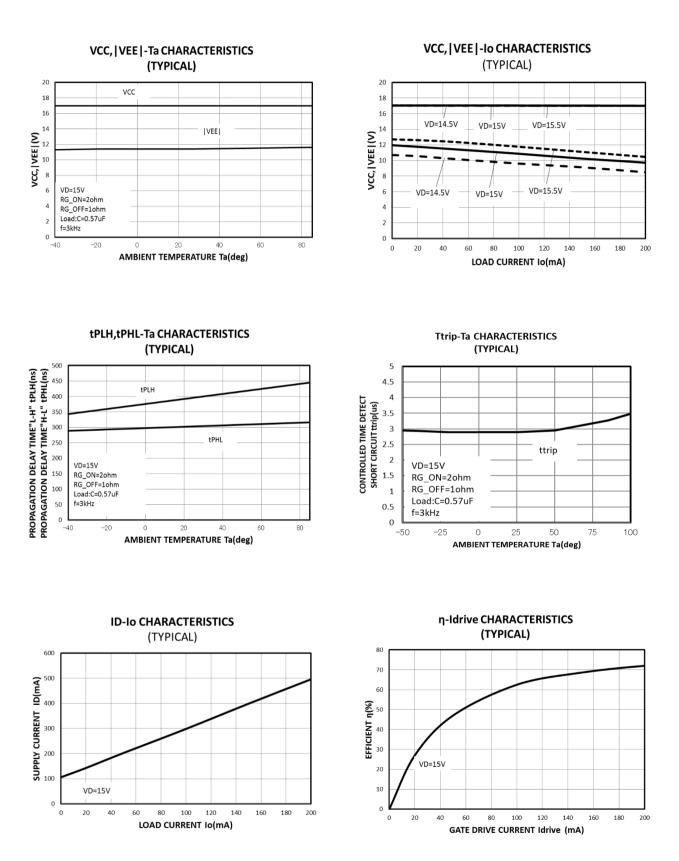


VLB505-01R

DRIVER FOR SIC-MOSFET MODULES

PERFORMANCE CURVES

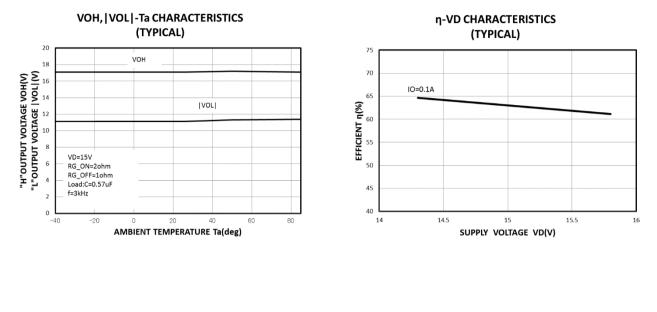
(Unless otherwise noted, Ta=25deg, VD=15V, RG_on=2 Ω ,RG_off=1 Ω ,f=3kHz) (ID: Input current for power supply, Idrive: gate average current, Io: DC load)

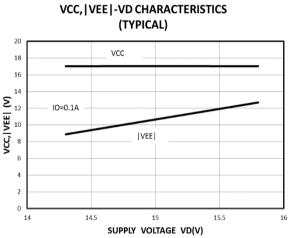


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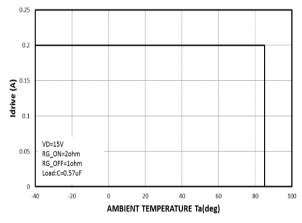
DRIVER FOR SIC-MOSFET MODULES







DERATING CHARACTERISTICS



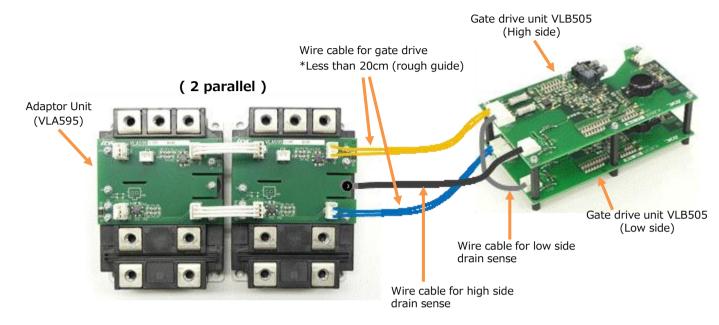
<Gate Drive Unit>



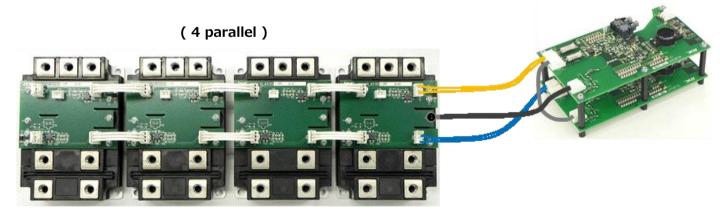
VLB505-01R

DRIVER FOR SIC-MOSFET MODULES

CONNECTION EXAMPLE 1



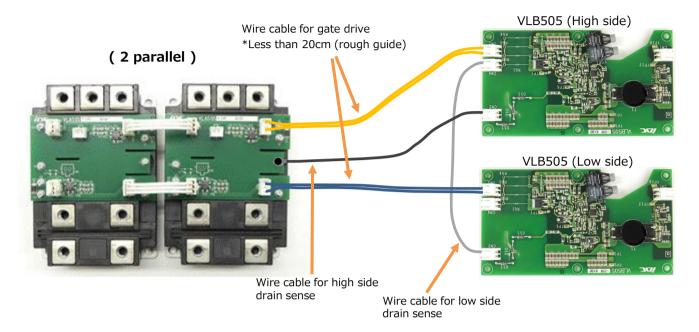
Note) When gate drive cable exceeds 20cm, please make it a twisted pair.



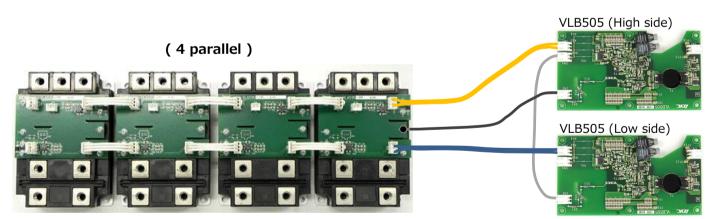


DRIVER FOR SIC-MOSFET MODULES

CONNECTION EXAMPLE2



Note) When gate drive cable exceeds 20cm, please make it a twisted pair.

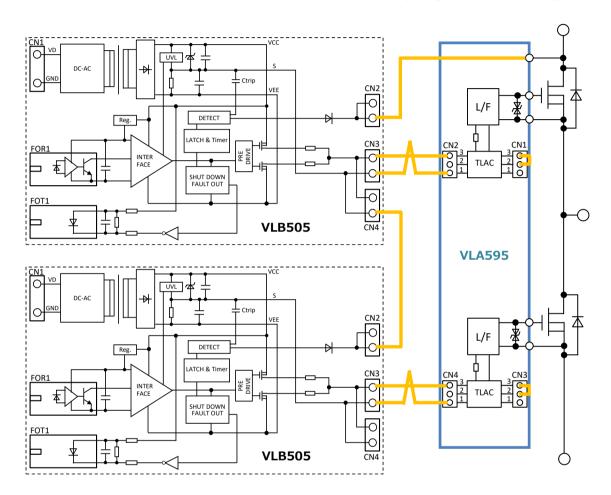


DRIVER FOR SIC-MOSFET MODULES



APPLICATION EXAMPLE1

(single connection 1)

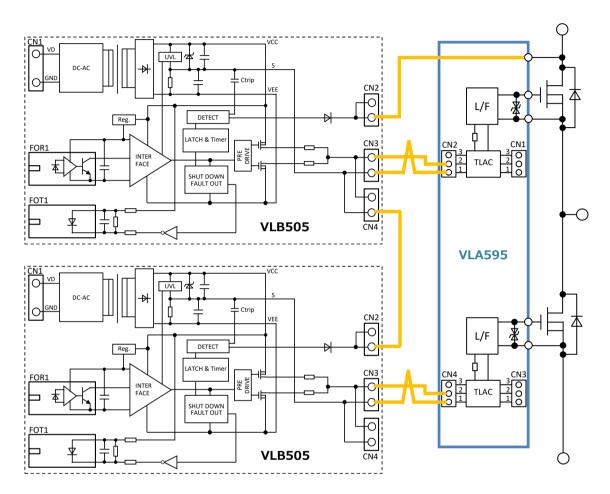


DRIVER FOR SIC-MOSFET MODULES



APPLICATION EXAMPLE2

(single connection 2)



DRIVER FOR SIC-MOSFET MODULES

(3 parallel connection)



APPLICATION EXAMPLE3

L/F ¥ L/F L/F 濲 DETECT þ ATCH & TI þ ¢ CN1 CN1 CN2 CN2 CN2 CN: PRE DRIVE 3 2 1 2 000 30 20 10 + TLAC SHUT DOWN FAULT OUT ю FOT Q VLB505 **VLA595 VLA595 VLA595** Ctrip ю L/F ₽ L/F 楽 L/F ₽ DETECT ATCH & Ti п CN PRE DRIVE INTE °21 001 + TLAC 2 SHUT DOWN FAULT OUT Ю FOT -0 ╪ VLB505 CN4

<Gate Drive Unit>

VLB505-01R

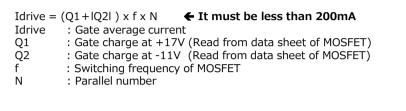
DRIVER FOR SIC-MOSFET MODULES

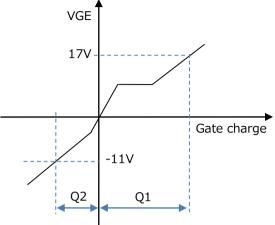
Gate charge characteristic of MOSFET



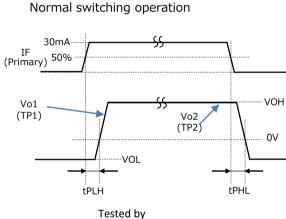
CALCULATION FOR GATE DRIVE CURRENT (GATE AVERAGE CURRENT)

This product has isolated DCDC converter built in for gate drive. The maximum output average current is 200mA. This current means maximum gate average current. **When you decide the switching frequency, please check the gate average current by next formula.**

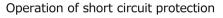


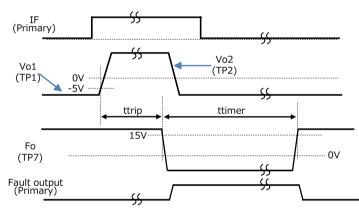


DEFINITION OF CHARACTERISTICS

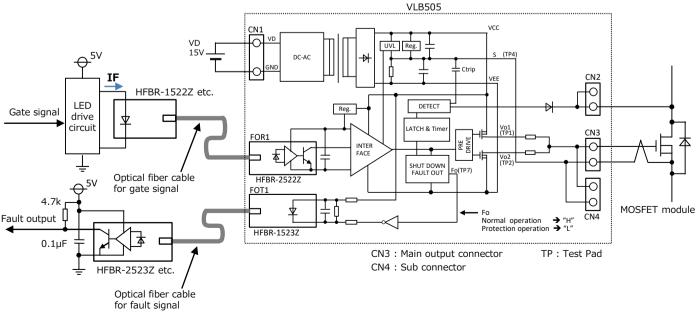


f=3kHz, Duty=50%





INTERFACE APPLICATION EXAMPLE



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DRIVER FOR SIC-MOSFET MODULES



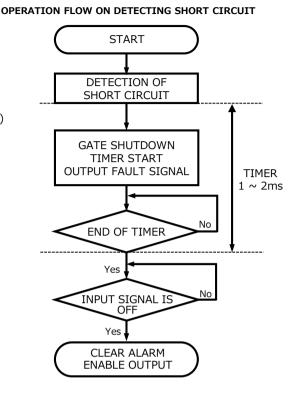
OPERATION OF PROTECTION CIRCUIT

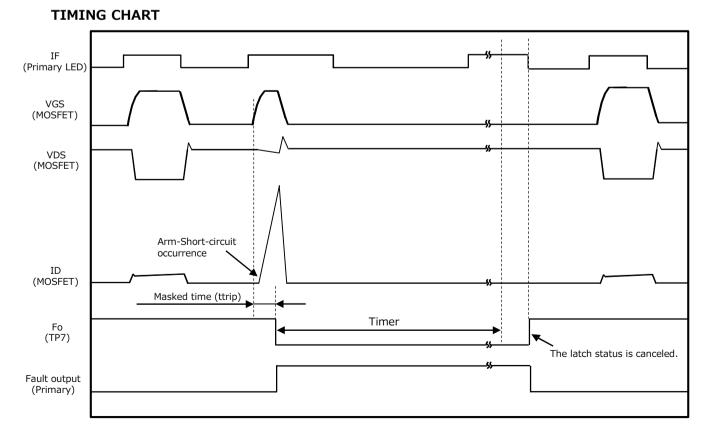
- (1) In case the gate voltage is "H" and the drain voltage is high, this drive unit will recognize the circuit as short circuit and reduce the gate voltage. Besides, put out fault signal ("L") which inform that protection circuit is operating at the same time from Fo terminal (Test Pad7).
- (2) The protection circuit reset and resort to ordinary condition if input signal is "OFF" when the premised 1~2msec passed. ("OFF" period needs 10us or more)
- (3) When the output rises, the masked time detect short circuit (ttrip) is set up so that on-time of MOSFET can be secured properly.

LATCH & TIMER RESET SYSTEM IN SHORT CIRCUIT PROTECTION CIRCUIT

Once the short-circuit protection circuit starts, it shuts down the gate output and keeps fault output, causing the latch status. This status is canceled if the input signal is OFF when specific time elapses after the activation of the shortcircuit protection circuit. Then, gate output depending on input signals becomes possible. If the input signal is ON when specific time elapses, the latch status is not canceled: it is canceled when the input signal becomes OFF.

As mentioned above, on the latch & timer reset system, the latch status is resulted after activation of the protection circuit and shutdown of the gate output. Therefore, during this period, gate output is not made no matter how much input signals are received. For this reason, it is possible to safely stop the entire equipment by sending error signals to the microcomputer during this period to stop all gate signals.





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DRIVER FOR SIC-MOSFET MODULES

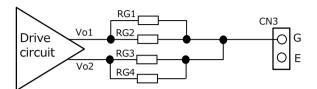
ABOUT MOUNTING GATE RESISTORS

There is not Gate Resistors on this unit at the initial state.

It is possible to install up to 4 resistors in mount area of gate resistor.

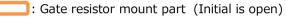
And there are some variations by combining resistors. There are some examples in the following chart, please refer to it and set the gate resistors.

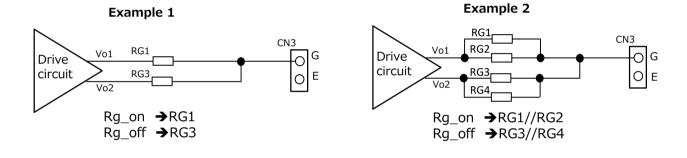
And please solder the chosen resistors.



Layout pattern connection on substrate







THE WAY TO CALCULATE GATE RESISTANCE VALUE OF PARALLEL CONNECTION

RG_ON/1elem. = Gate ON resistance value per one element = Rb + (N x Rg_on) RG_OFF/1elem. = Gate OFF resistance value per one element = Rb + (N x Rg_off)

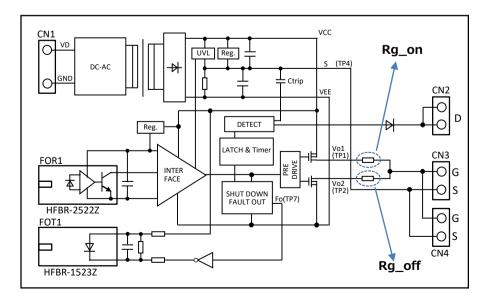
Rb : Balance resistance value on adaptor unit

N : Parallel number of modules

Note)

Rg_on : Gate ON resistance value on VLB505

Rg_off : Gate OFF resistance value on VLB505





DRIVER FOR SIC-MOSFET MODULES

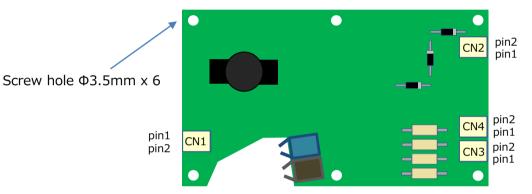
DETAILS OF CONNECTOR

CN1: 53259-0229 (Molex)		
Pin No.	Signal	
1	VD	
2	GND	

CN2: 53259-0229 (Molex)		
Pin No.	Signal	
1	Drain	
2	Drain	

CN3: 53259-0229 (Molex)		
Pin No.	Signal	
1	Source	
2	Gate	

CN4: 53259-0229 (Molex)		
Pin No.	Signal	
1	Source	
2	Gate	

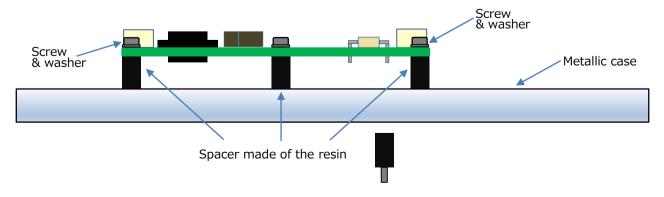


We recommend following parts or equivalent product for wire cable

HOUSING	TERMINAL	Maker	
51067-0200	50217-8100	Molex	

INSTALLATION OF THE DRIVE UNIT ON METALLIC CASE

When fixing this drive unit on a metallic case, please use the spacer made of the resin.



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FOR SAFETY USING

Great detail and careful attention are given to the production activity of Hics, such as the development, the quality of production, and in it's reliability. However the reliability of Hics depends not only on their own factors but also in their condition of usage. When handling Hics, please note the following cautions.

	CAUTIONS	
Packing	The materials used in packing Hics can only withstand normal external conditions. When exposed to outside shocks, rain and certain environmental contaminators, the packing materials will deteriorates. Please take care in handling.	
Carrying	 Don't stack boxes too high. Avoid placing heavy materials on boxes. Boxes must be positioned correctly during transportation to avoid breakage. Don't throw or drop boxes. Keep boxes dry. Avoid rain or snow. Minimal vibration and shock during transportation is desirable. 	
Storage	 When storing Hics, please observe the following notices or possible deterioration of their electrical characteristics, risk of solder ability, and external damage may occur. 1) Devices must be stored where fluctuation of temperature and humidity is minimal, and must not be exposed to direct sunlight. Store at the normal temperature of 5 to 30 degrees Celsius with humidity at 40 to 60%. 2) Avoid locations where corrosive gasses are generated or where much dust accumulates. 3) Storage cases must be static proof. 4) Avoid putting weight on boxes. 	
Extended storage	When extended storage is necessary, Hics must be kept non-processed. When using Hics which have been stored for more than one year or under severe conditions, be sure to check that the exterior is free from flaw and other damages.	
Maximum ratings	To prevent any electrical damages, use Hics within the maximum ratings. The temperature, current, voltage, etc. must not exceed these conditions.	
Polarity	To protect Hics from destruction and deterioration due to wrong insertion, make sure of polarity in inserting leads into the board holes, conforming to the external view for the terminal arrangement.	



DRIVER FOR SIC-MOSFET MODULES

Keep safety first in your circuit designs!

·ISAHAYA Electronics Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1) placement of substitutive, auxiliary circuits, (2) use of non-flammable material or (3) prevention against any malfunction or mishap.

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